HVC359

Variable Capacitance Diode for VCXO

HITACHI

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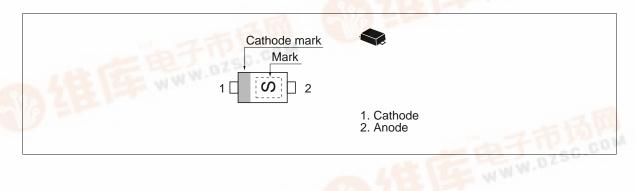
Features

- High capacitance ratio and good C-V linearity.
- To be usable at low voltage.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HVC359 | S | UFP |

Outline





HVC359

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

| Item | Symbol | Value | Unit |
|----------------------|--------|-------------|------|
| Reverse voltage | V_R | 15 | V |
| Junction temperature | Tj | 125 | °C |
| Storage temperature | Tstg | -55 to +125 | °C |

Electrical Characteristics (Ta = 25° C)

| Item | Symbol | Min | Тур | Max | Unit | Test Condition |
|-------------------|-----------------|------|-----|------|------|---|
| Reverse current | I _{R1} | _ | _ | 10 | nA | $V_R = 10V$ |
| | I _{R2} | _ | _ | 100 | | V _R = 10V, Ta = 60 °C |
| Capacitance | C ₁ | 24.8 | _ | 29.8 | pF | $V_R = 1V$, $f = 1 MHz$ |
| | C ₄ | 6.0 | _ | 8.3 | | $V_R = 4V, f = 1 MHz$ |
| Capacitance ratio | n | 3.0 | _ | _ | _ | C ₁ /C ₄ |
| Series resistance | r_s | _ | _ | 1.5 | Ω | V _R = 4V, f = 100 MHz |
| ESD-Capability*1 | Å\ | 80 | _ | _ | V | C=200pF , Both forward and reverse direction 1 pulse. |

Notes 1. Failure criterion ; IR ≥ 20nA at VR =10 V

Main Characteristic

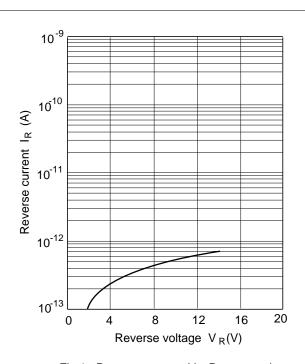


Fig.1 Reverse current Vs. Reverse voltage

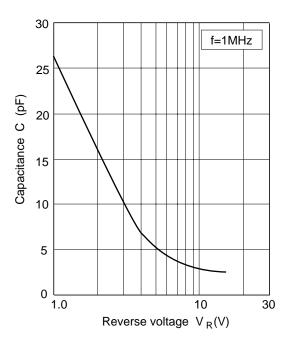
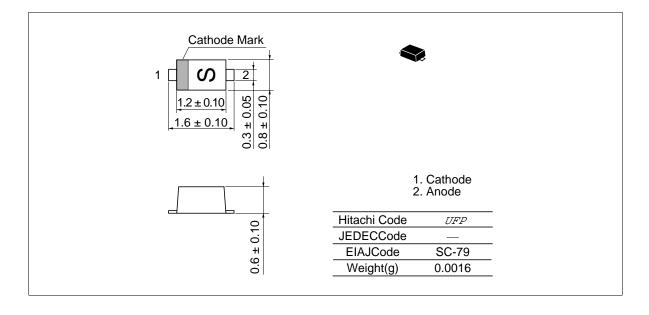


Fig.2 Capacitance Vs. Reverse voltage

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Package Dimensions

Unit: mm



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